

File View Edit Tools Window Help  
 Close Minimize Maximize

Active  
 L1: (155) ((cell memory) near2 (area region section portion D))  
 L2: (100531) cmos  
 L3: (94) 1 and 2  
 L4: (22678) pmos with nmos  
 L5: (70) 3 and 4  
 L6: (110) (257/214).CCLS

Failed  
 Saved  
 (1) 09/948877  
 (1736) "KONINKLIJKE PHILIPS".as  
 (2) 10/253779  
 (1) 10/234501  
 (37717) n-well pmos  
 (43184) p-well nmos  
 (1979052) peripher\\$2 logic  
 (2357117) cell memory  
 (1821711) (peripher\\$2 logic 0 ) with (cell memory)  
 (3810307) region area  
 (82488) (cell memory) adj2 (region area)  
 (7362802) (area region section portion )  
 (215405) (cell memory) near2 (area region section portion D))  
 (270282) (peripher\\$2 logic 0 ) near2 (area region section portion D))  
 (809848) polysilicon poly adj silicon silicon  
 (3102552) metal

Database: USPTO:US:PCPUB: EPO: JPO: DPERVENT: IBM: TDB  
 Default operator: OR  
 Plurals  
 Highlight all instances initially

10/253779

*Feb. 2004*

U	I	Inventor	Document Type	Title	Current Status	XN	Reviewed	S	C	I	P	Image Doc.	P
<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 2003008 2003012	CMOS of semiconductor device and method f 257/389 257/E21.63	<input type="checkbox"/>	US 2003008	<input type="checkbox"/>						
<input type="checkbox"/>	<input type="checkbox"/>	Cho, Heung J	US 6642132 200312	Cmos of semiconductor device and method f 438/502,257/315	<input type="checkbox"/>	US 6642132	<input type="checkbox"/>						

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